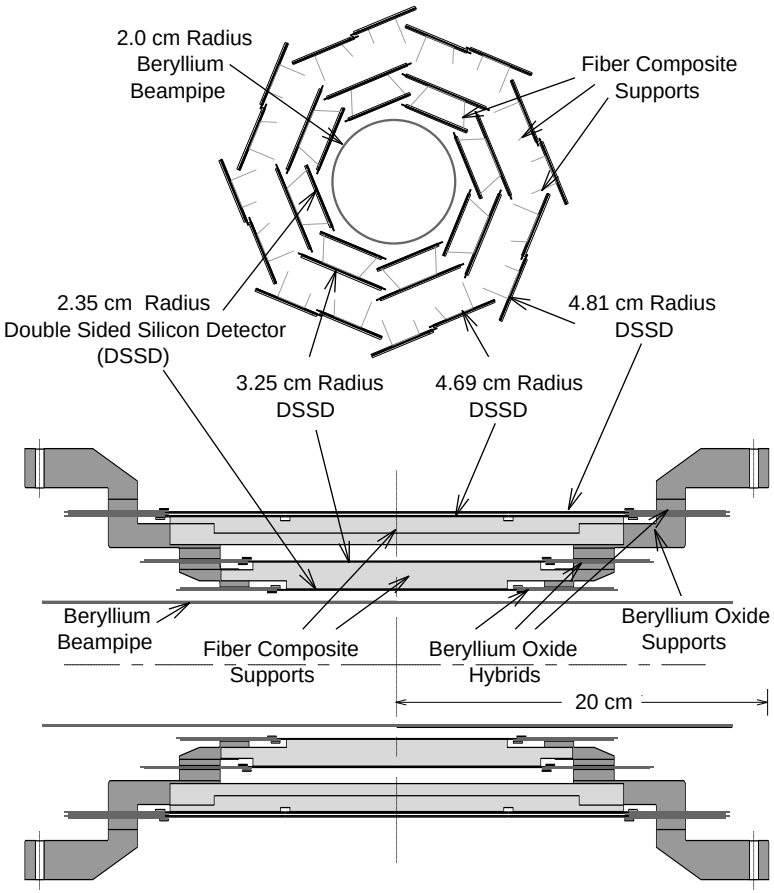
CLEO-II/SVX Upgrade

- 3-layers of Double Sided Silicon
  - rϕ: S/N $\approx 15/1$, $\sigma = 15\mu m$
  - rz: S/N $\approx 10/1$, $\sigma = 22\mu m$
  - $D^0 : \sigma_\tau \approx 0.4\tau$
  - $D^{*+} \rightarrow D^0\pi^+$
    - $\sigma_{\delta M}$: 750 KeV (CLEO-II)
      $\rightarrow$ 100-250 KeV (CLEO-II/SVX)
- Helium/Propane Replaces Argon Ethane as Drift Chamber(DR) Gas
  - DR X_0 reduced by factor of 0.61
  - D^0 mass σ: 12.2 MeV (CLEO-II)
    $\rightarrow$ 6.9 MeV (CLEO-II/SVX)
    $\rightarrow$ 4.8 MeV (just gas)
- 5.5 fb^{-1} : so far 9,200
  $D^{*+} \rightarrow D^0\pi^+$, $D^0 \rightarrow K^-\pi^+$
- 8+ fb^{-1} expected